I. Number	Hits	Search Text.	DB	Time stamp
13		troutman-ronald-roy.in. and diffusion and	USPAT;	2003710713 12:20
		fabricated	US-PGPUB; EPO; JPO;	
1	i	I	DERWENT;	1
1			IBM TOB	1
14	2	6157356.pn.	USPAT;	2003/10/13 12:22
			US-PGPUH; EPO; JPO;	1
			DERWENT;	
			IBM TDB	1
15	. 1	6157356.pn.	USPAT;	2003/10/13 12:22
		r.	US-PGPUB;	1
			. EPO; JPO; 1BM TDB	1
16	. 1	. 6157356.pm. and silicon	USPAT;	2003/10/13 12:22
. 10		. ozoroso.p.n. una sarreon	US-PGPUB;	1 1005/10/15 10122
			EPO; JPO;	1
1			IBM_TDB	1
. 17	. 3	(organic near3 (electroluminesc\$8 EL)) and	USPAT;	2003/10/13 12:25
1		'(drying dry dessicant) and cover and gas and ceramic same (glass silica) and	US-PGPUB	1
		(active adj matrix transistor tft (et)	1	
1		'near5 (monocrystalline mono adj	1	1
1		'crystalline) not single adj crystal	r	1
1.8	3	(organic near3 (electroluminesc\$8 EL)) and		2003/10/13 12:27
i		drying dry dessicant) and cover and gas and ceramic same (glass silica) and	US-PGPUB; EPO; JPO;	1
1		(active adj matrix transistor tft fet)	. DERWENT;	
		near5 (monocrystalline mono adj	. IBM TDB	
1		crystalline) not single adj crystal		
. 19	. 3	(organic near3 (clectroluminesc\$8 EL)) and		2003/10/13 12:27
			US-PGPUB;	* ·
		and ceramic same (glass silica) and (active adj matrix transistor tft fet)	'EPO; JPO; DERWENT;	1.00
		near5 (monocrystalline mono adi	IBM TDB	
		crystalline) not single adj crystal		
20	. 0	(organic near3 (electroluminesc\$8 EL)) and	USPAT;	2003/10/13 12:27
		(drying dry dessicant) and cover and gas	US-PGPUB;	di
		with (space gap) and ceramic same (glass silica) and (active adj matrix transistor	EPO; JPO; DERWENT;	
		tft fet) nearb (monocrystalline mono adj	IBM TOB	
		crystalline) not single adj crystal		
21		troutman-ronald-roy.in. and diffusion and	USPAT;	. 2003/10/13 13:41 [
	1	silicon	US-PGPUH; EPO; JPO;	
			DERWENT;	
			IBM TDB	i
1.22	2	troutman-ronald-roy.in. and diffusion and	USPAT;	. 2003/10/13 12:49 4
1		silicon and well	US-PGPUB;	
1	;		EPO; JPO; DERWENT;	
			IBM TDB	
23	2	troutman-ronald-roy.in. and diffusion and	USPAT;	2003/10/13 13:40
	i .	silicon and (well body)	· US-PGPUB;	-
	1		· EPO; JPO;	
			DERWENT;	1
24	2143	(313/500,504,505,512).CCLS.	IBM TDB USPAT;	2003/10/13 13:41
			US-PGPUB	1 2000/20/10 20.41
25	1201		USPAT;	, 2003/10/13 13:41
. 26			· US-PGPUB	
26	611	(345/36,76).CCLS.	USPAT; US-PGPUB	2003/10/13 13:41
1- 1	229	(445/25).CCLS.	· USPAT	2002/08/28 14:30
-		(313/512).CCLS.	USPAT	2002/08/28 14:39
! - !		09671654.ap.	USPAT;	2002/08/28 14:39
1 1			US-PGPUB;	1
1			EPO; JPO; DERWENT;	1
4			· IBM TDB	1
50 - 5 Text 5				1.11.2

		9671654.ap.	USPAT;	2002/08/28	14:39
			US-PGPUB;	1	
		i	EPO; JPO; DERWENT;	1	
	4		IBM TOB	T.	
_	229	(445/25).CCLS.	. USPAT	12002/08/28	14:48
_		((313/512) or (445/25)).CCLS.	USPAT;	. 2002/08/28	
	1	( ((373) 321) 32 ((13723)) (3323)	EPO; JPO;		
	1	1	DERWENT;		
	1		TBM TDB	1	
-	1 17	(((313/512) or (445/25)).CCLS.) and active		2002/08/28	14:55
	1	adj matrix	. US-PGPUB;	Ŷ.	
	1	1	. EPO; JPO;		
			DERWENT;	1	
	1 12		IBM_TDB		
-		((((313/512) or (445/25)).CCLS.) and	USPAT;	2002/08/28	14:56
		active adj matrix) and crystal	US-PGPUB;		
			. EPO; JPO; . DERWENT;	1	
			. IBM TDB		
_		((((313/512) or (445/25)).CCLS.) and	USPAT;	: 2002/08/28	14.58
	1	'active adj matrix) and single adj crystal	'US-PGPUB;	12002/00/20	14.50
		I	: EPO; JPO;	1	
			DERWENT;	1	
			IBM TDB	1	
-	3	5672083.URPN.	USPAT	2002/08/28	14:57
-	. 1	((((313/512) or (445/25)).CCLS.) and	. USPAT;	2002/08/28	15:01
	1	active adj matrix) and (field adj effect	US-PGPUB;	1	
		adj transistor FET)	EPO; JPO;	i	
		i	'DERWENT;		
	4		· IBM_TDB	7	
-	. 0	(257.\$).ccis.	USPAT;	2002/08/28	15:01
			US-PGPUB;		
		i	EPO; JPO;		
	1		DERWENT;		
	124761	(257/\$).ccls.	'IBM_TDB 'USPAT;	2002/08/28	10.00
_	124/31	(23//9).CC.15.	US-PGPUB;	2002/08/20	13:07
			· EPO; JPO;		
			DERWENT;	1	
			. IBM TDB		
-	66945	(313/\$).ccls.	USPAT;	12002/08/28	15:02
		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	US-PGPUB;	1	
	1		EPO; JPO;	k.	
	1	i.	DERWENT;		
			1BM TDB	'	
-		((257/\$).ccls.) and active adj matrix and	USPAT;	2002/08/28	15:04
	1	(organic with EL) and gate with (field adj	US-PGPUB;		
		effect adj transistor FET)	EPO; JPO;	i	
			DERWENT;		
		(435346)	IBM TDB		11 20
-	5	((257/\$).ccls.) and active adj matrix and	USPAT;	. 2002/08/28	15:32
	1	(organic with EL) and gate with (field adj	US-PGPUB; EPO; JPO;	1	
	i	crystal	- DERWENT;	1	
		0.1000.	IBM TDB		
_	. 0	((313/\$).ccls.) and active adi matrix and	USPAT:	2002/08/28	15:25
		(organic with EL) and gate with (field adj		. 2002/00/20	
	1	offect adj transistor FET) and single adj	EPO; JPO;	4	
		crystal	DERWENT;		
			: IBM TDB		
-		((257/57) or (257/59) or (257/66) or	. USPAT;	1 2002/08/28	16:14
		(257/66) or (257/72) or (257/347) or	· US-PGPUB;		
	1	(257/350)).CCLS.	EPO; JPO;		
			DERWENT;		
	4.		IBM_TDB		

v =	,		(((257757) or (257/59) or (257/66) or	USPAT;	2002/08/29 08:3	36 1
1	- 1		(257/66) or (257/72) or (257/347) or	US-PGPUB;	1	- 1
1	1		(257/350)).CCLS.) and active adj matrix	EPO; JPO;	1	1
	1		and (organic with EL) and gate with (field	DERWENT;		
1			adj effect adj transistor FET) and single	IBM_TDB	I .	-
	1		adj crystal	USPAT:	2003/09/12 13:3	
		4350	yamazaki-shunpei.in. or arai-yasuyuki.in.	US-PGPUB;	2003/09/12 13:.	14
î			1	'EPO; JPO;		1
			F.	DERWENT;		1
1			I .	TBM TDB		
		4178	'yamazaki-shunpei.in.	USPAT;	2002/08/28 15:3	31
				US-PGPUB;	1	- 1
	1			EPO; JPO;	1	- 1
i			·	DERWENT;	1	- 1
		0.13		1BM_TDB		١ .
			yamazaki-shunpei.in. or arai-yasuyuki.in.	USPAT	2003/06/11 18:0	
	1	11/1	yamazaki-shunpei.in. or arai-yasuyuki.in.	USPAT; US-PGPUB	2003/10/03 20:	12
	1	0	(yamazaki-shunpei.in. or	: USPAT;	12002/08/28 15:3	33.
	1		arai-yasuyuki.in.) and active adj matrix	US-PGPUB;	7002/00/20 13	
3	1		and (organic with EL) and gate with (field		I .	i
1				: DERWENT;	t .	
			. adj crystal	1BM TDB		- 1
-	i i	1	, (yamazaki-shunpei.in. or	USPĀT;	2002/08/28 15:3	33 '
1	1		arai-yasuyuki.in.) and active adj matrix	US-PGPUB;		- 1
ī	i		and (organic with EL) and gate with (field	EPO; JPO;		
5			adj effect adj transistor FET) and single	DERWENT;		-
1	1		, adj crystal	'IBM_TDB		'
	1		, 1089595.URPN.	USPAT	2002/08/28 15:3	
	1		, (((257/57) or (257/59) or (257/66) or . (257/66) or (257/72) or (257/347) or	USPAT;	2002/08/28 16:3	15
	1		. (257/350)).CCLS.) and active adj matrix	US-PGPUB; EPO; JPO;	1	- 1
			and (organic with EL) and gate with (field		1	- 1
1			adj effect adj transistor FET mostft) and	IBM TDB	1	
	1		single adj crystal	1 2211_100		
1 =		5136	((257/57) or (257/59) or (257/66) or	USPAT;	2002/08/29 13:5	56 <sup>1</sup>
1			(257/66) or (257/72) or (257/347) or	US-PGPUB;	1	1
			, (257/350) or (313/512) or (445/25)).CCLS.	EPO; JPO;	1	1
	1		I .	DERWENT;	i .	- 1
1	1			IBM TDB		1
. ~				USPAT;	2002/08/28 16:1	15
				US-PGPUB;	1	- 1
	- ;		and active adj matrix and (organic with	F.PO; JPO; DERWENT;	1	- 1
			EL) and gate with (field ad) effect adj	IBM TOB		
			transistor FET mostft) and single adj	100.100		- 1
			crystal	1	1	- 1
-		2	("6153893"   "6246070").PN.	USPAT	2002/08/28 16:2	27 !
-	1		((257/57) or (257/59) or (257/66) or	'USPAT;	, 2002/08/29 10:0	00
	1		(257/66) or (257/72) or (257/347) or	US-PGPUB;	t .	
1			(257/350) or (313/512) or (445/25)).CCLS.	EPO; JPO;	1	- 1
1				DERWENT;	1	
	7	2 '	(#6351010#) (%)	IBM_TDB		
1	1	3 ,	("6351010").PN.	USPAT;	,2002/08/29 07:3	0/1
Ī				US-PGPUB; EPO; JPO;		3
				DERWENT;		
	- 1			IBM TDB		
-	1		("6153893"   "6246070").PN.	USPĀT	2002/08/29 07:4	7.
-	1		(("6153893"   "6246070").PN.) and organic	USPAT	2002/08/29 07:4	
1	- 1		with (EL electroluminescence			- 1
			electroluminoscent)	1		t.
-		0	(("6153893" ! "6246070").PN.) and organic	USPAT	2002/08/29 07:4	16:
			same (RL electroluminescence		I .	1
			electroluminoscent)			
		3	semiconductor-energy-laboratory.as.	USPAT	2002/08/29 07:4	ισ.

77		- a-	semiconductor-energy-laboratory.as.	USPAT;	2002/08/29 07:51
1		,		US-PGPUB;	, 4042/00/27 01/03 (
1				EPO; JPO;	1 1
	i			DERWENT;	1
	1			IBM TDB	
-	1	7	sony.as, and single adj crystal and active		2002/08/29 07:55
v.	1			US-PGPUB;	
	1		effect adj transistor)	EPO; JPO;	
	1			DERWENT;	
				IBM TDB	1
-		3	sony.as, and single adj crystal and active	. USPĀT;	2002/08/29 08:00
1	- 1		adj matrix and gate with (FET field adj	US-PGPUB;	
			effect adj transistor) and (organic with	EPO; JPO;	N. C.
1				. DERWENT;	1
1			electroJuminescence))	· IBM TDB	1
-		0	sony.as. and single adj crystal and active		2002/08/29 08:00
	,			US-PGPUB;	
4				EPO; JPO;	Ý
				DERWENT;	7
				IBM TDB	
		2		· USPAT;	2002/08/29 08:38
	1		(257/66) or (257/72) or (257/347) or	US-PGPUB;	
	1			EPO; JPO;	
			and active adj matrix and (organic with	· DERWENT;	
			EL) and gate with (field adj effect adj	' IBM TDB	1
	i		transistor FET) and single adj crystal		1
	1		(((257/57) or (257/59) or (257/66) or	USPAT;	2002/08/29 08:43
	1		(257/66) or (257/72) or (257/347) or	US-PGPUB;	
			(257/350) or (313/512) or (445/25)).CCLS.)	'EPO; JPO;	
			and active adj matrix and (organic with	DERWENT;	· ·
			(EL electroluminescenco	TBM TDB	
	1		electroluminescent)) and gate with (field		
			adj effect adj transistor FET) and single		1
			adj crystai	1	· 7
-			(((257/57) or (257/59) or (257/66) or	USPAT;	2002/08/29 08:44
			(257/66) or (257/72) or (257/347) or	US-PGPUB;	. 2002, 00, 25
				EPO; JPO;	
			and active adj matrix and (organic with	DERWENT;	1
			(EL electroluminescence	- 1BM TDB	
	1		electroluminoscent)) and gate with (field		
			adj effect adj transistor FET bottom adj		
			gate top adj gate) and single adj crystal	v.	1
-			(((257/57) or (257/59) or (257/66) or	USPAT;	12002/08/29 08:44
			(257/66) or (257/72) or (257/347) or	'US-PGPUB;	
	1		(257/350) or (313/512) or (445/25)).CCLS.)	EPO; JPO;	F .
			and active adj matrix and (organic with	DERWENT;	
			(EL electroluminescence	'IBM TDB	
			electroluminescent)) and gate with (field		
,			adj effect adj transistor FET bottom adj		a. I
			gate top adj gate) and single adj crystal		·
			and gas		- 1
-			(((257/57) or (257/59) or (257/66) or	'USPAT;	. 2002/08/29 10:17
	1		(257/66) or (257/72) or (257/347) or	US-PGPUB;	,
			(257/350) or (313/512) or (445/25)), CCLS.)	EPO; JPO;	
			and active adj matrix and (organic with	DERWENT;	t · · · · · · · · · · · · · · · · · · ·
			(EL electroluminescence	IBM TDB	
			electroluminoscent)) and gate with (field		
			adj effect adj transistor FET bottom adj		
	1		gate top adj gate) and single adj crystal	I .	
	1		and (inert adj gas)	i	
-	1		(((257/57) or (257/59) or (257/66) or	USPAT;	12002/08/29 09:25
	1		(257/66) or (257/72) or (257/347) or	US-PGPUB;	
		- 1	(257/350) or (313/512) or (445/25)).CCLS.)	EPO; JPO;	
			and TFT with FET	DERWENT;	
				IBM TOB	
-	4	1 '	6274887,URPN.	USPAT	2002/08/29 09:55
-	ì	14	("5247190"   "5399502"   "5401982"	USPAT	2002/08/29 09:56
			"5576556"   "5612234"   "5620905"		
	1		"5643826"   "5710606"   "5719065"		. '
			"5736414"   "5789762"   "5923962"		
			"5926735"   "5959313").PN.		1

	1	0-	7 (("5247190"   "5399502"   "5401982"	USPAT;	2002/08/29	09:59
			"5576556"   "5612234"   "5620905"	US-PGPUB;		
	i		"5643826"   "5710606"   "5719065"	EPO; JPO;	4	-1-
			1 "5736414"   "5789762"   "5923962"	DERWENT';	3	
	-		. "5926735"   "5959313").PN.) and active adj	'IBM TOB	1	1
1				120-100		
			matrix and (organic with (EL		1	
I			electroluminescence electroluminescent))			
	1		, and gate with (field adj offect adj			1
	7		transistor FET bottom adj gate top adj	111		
			, gate) and single adj crystal and (inert	1	1	
			, adj gas)	1		
' -		0	(("5247190"   "5399502"   "5401982"	USPAT;	'2002/08/29	09:59
			"5576556"   "5612234"   "5620905"	· US-PGPUB;		1
l .			' "5643826"   "5710606"   "5719065"	EPO; JPO;	1	1
			· "5736414"   "5789762"   "5923962"	DERWENT;		1
			. "5926735"   "5959313").PN.) and active adj	IBM TDB		
			matrix and (organic with (EL		1	
	1		, electroluminescence electroluminescent))		1	
			and gate and single adj crystal and	i	1	
			(inert adj gas)	1	1	
-		492	(((257/57) or (257/59) or (257/66) or	USPAT;	, 2002/08/29	10:02
			(257/66) or (257/72) or (257/347) or	US-PGPUB;	1	
			(257/350) or (313/512) or (445/25)).CCLS.)	EPO; JPO;	T.	3
			and inert gas with organic adj EL.	DERWENT;		
	1		and incre gas with organize day on	IBM_TDB		
1		0	(((257/57) or (257/59) or (257/66) or	USPĀT;	12002/08/29	10.00 1
		,			2002/08/29	10:02
	,		(257/66) or (257/72) or (257/347) or	US-PGPUB;	1	i.
			(257/350) or (313/512) or (445/25)).CCLS.)	EPO; JPO;	1	
	1		and inert adj gas with organic adj EL	DERWENT;	ì	1
	1		·	IBM TDB	1	
-			· (((257/57) or (257/59) or (257/66) or	USPAT;	2002/08/29	10:03
1			(257/66) or (257/72) or (257/347) or	US-PGPUB;		
			(257/350) or (313/512) or (445/25)).CCLS.)	EPO; JPO;	1	
			and inert adj gas with organic adj EL same	'DERWENT;		- 1
			oxidize	· IBM TDB		1
: -	1	0	(((257/57) or (257/59) or (257/66) or	USPAT;	2002/08/29	10:03
			(257/66) or (257/72) or (257/347) or	US-PGPUB;	2	
	1		'(257/350) or (313/512) or (445/25)).CCLS.)	EPO; JPO;	1	
	1			DERWENT;	į.	1
	1.0		'(oxidize deteriorate)	IBM TDB	1	i i
_	4	0	'(((257/57) or (257/59) or (257/66) or	. USPAT;	. 2002/08/29	10.20
			'(257/66) or (257/72) or (257/347) or	US-PGPUB;	2001,00,25	10.120
			(257/350) or (313/512) or (445/25)).CCLS.)	EPO; JPO;		1
			and active adj matrix and (organic with	DERWENT;	'	
1			(EL electroluminescence	IBM TDB	'	1
			'electroluminescent)) and gate with (field	100-100	'	
			'adj effect adj transistor FET bottom adj	1		
	-				1	
			gate top adj gate) and single adj crystal		1	1
		0	and (rare adj gas)	Litration	1 0000 (00 (00	10.01
	,	8	(((257/57) or (257/59) or (257/66) or	USPAT;	2002/08/29	10:21
1			(257/66) or (257/72) or (257/347) or	US-PGPUB;	1	1
			(257/350) or (313/512) or (445/25)).CCLS.)	'EPO; JPO;	1	1
			and active adj matrix and (organic with	'DERWENT;		
			(EL electroluminescence	! IBM TDB		
			'electroluminescent)) and gate with (field	*		
			adj effect adj transistor FET bottom adj			
			gate top adj gate) and single adj crystal	1		
			and (helium he argon ar krypton kr xenon	f .		1
			xe nitrogen ni)		1	1
-		3	(((257/57) or (257/59) or (257/66) or	· USPAT;	1 2002/08/29	10:24 1
			(257/66) or (257/72) or (257/347) or	EPO; JPO;		1
				DERWENT;	*	1
	1		and active adj matrix and (organic with	. IBM TDB	1	
			(EL electroluminescence		1	1
	,		electroluminescent)) and gate with (field		T.	1
			adj effect adj transistor FET bottom adj		¥	1
			gate top adj gate) and single adj crystal			i
	1		and (helium he argon ar krypton kr xenon			
			'xe nitrogen ni)	4	i company	Ÿ
5000			e de la grande de la	·		'

-1-	- +	 3	(((257/57) or (257/59) or (257/66) or	USPAT;	2002/08/29 11:12
		-	(257/66) or (257/72) or (257/347) or	EPO; JPO;	
	1		(257/350) or (313/512) or (445/25)).CCLS.)	DERWENT;	1
		- 1	and active adj matrix and (organic with	IBM_TDB	1 7
			(EL electroluminescence		\$- ·
			electroluminescent)) and gate with (field		
1	1.		adj effect adj transistor FET bottom adj		
1			gate top adj gate) and single adj crystal	1700310	2002/08/29 10:26
	7			USPAT;	2002/08/29 10:26
1		-	(257/66) or (257/72) or (257/347) or	EPO; JPO; DERWENT;	
			(257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with	IBM TDB	
1			(EL clectroluminescence	. 1100-100	
		-	electroluminescent)) and gate with (field	I .	
			adj effect adj transistor FKT bottom adj	i .	
'			gate top adj gate) and single adj crystal		. 1
1			) and (helium he argon ar krypton kr xenon		. 1
1			xe nitrogen ni)		à l
<u>'</u> -			((((257/57) or (257/59) or (257/66) or	USPAT;	2002/08/29 10:27 L
i i			(257/66) or (257/72) or (257/347) or	EPO; JPO;	1
Ý.			(257/350) or (313/512) or (445/25)).CCLS.)	DERWENT;	
			and active adj matrix and (organic with	IBM_TDB	1
i	,		(EL electroluminescence	1	
	,		electroluminescent)) and gate with (field	1	
	1		adj effect adj transistor FET bottom adj	1	
			gate top adj gate) and single adj crystal	i .	
	,		) and (helium he argon ar krypton kr xenon	1	1
<i>t</i> _	1		xe nitrogen n) ((((257/57) or (257/59) or (257/66) or	USPAT;	2002/08/29 10:28
	1		(257/66) or (251/72) or (257/347) or	EPO; JPO;	2002/00/29 10.20
1			(257/350) or (313/512) or (445/25)).CCLS.)	DERWENT;	
1	1		and active adj matrix and (organic with	TBM TDB	
			(EL electroluminescence	1	1
1		,	electroJuminescent)) and gate with (field	I .	1
1	1		adj effect adj transistor FET bottom adj	I .	1
1	1		gate top adj gate) and single adj crystal	t .	1
	,		) and (helium he argon ar krypton kr xenon		1
1	1	- 1	xe nitrogen n) and (barium adj oxide		1
1			silica adj gel drying)		
	1.		((((257/57) or (257/59) or (257/66) or	USPAT;	2002/08/29 10:28
1			(257/66) or (257/72) or (257/347) or	EPO; JPO;	1
			(257/350) or (313/512) or (445/25)).CCLs.)	DERWENT;	
	1	- 1	and active adj matrix and (organic with	'IBM_TDB	1
	1		(EL electroluminescence electroluminescent)) and gate with (field		1
	1		adj effect adj transistor FET bottom adj		
1			gate top adj gate) and single adj crystal	1	1
			and (helium he argon ar krypton kr xenon		1
i .		- 1	xe nitrogen ni)) and (helium he argon ar		1
			krypton kr xenon xe nitrogen n) and	1	1
			(barium adj oxide silica adj gel drying)		
v -	1		((((257/57) or (257/59) or (257/66) or	USPAT;	,2002/08/29 10:29
1			(257/66) or (257/72) or (257/347) or	EPO; JPO;	
		- 1	(257/350) or (313/512) or (445/25)).CCLs.)	DERWENT;	
				IBM_TDB	
			(EL electroluminescence	1	1 3
	- 1		electroluminescent)) and gate with (field	1	
			adj effect adj transistor FET bottom adj	i e	The state of the s
'		- 1	gate top adj gate) and single adj crystal		1
			and (helium he argon ar krypton kr xenon	1	ģ., I
	- 1		xe nitrogen ni)) and (helium he argon ar		
			krypton kr xenon xe nitrogen n inert adj		
			gas inert adj gas) and (barium adj oxide silica adj gel drying)		
		 -'	Sarriaginal Man affendi		N=

C(257/66) or (257/75) or (257/56) or (257/347) or (257/36) or (313/512) or (445/25)).CCLS.)   DERMENT;   and active adj matrix and (organic with   IEE. electroluminescence					
(257/350) or (313/512) or (445/25)).CCLS.   DERWENT;   and active adj matrix and (organic with (field extraordinal extra		, 1	i ((((257/57) or (257/59) or (257/66) or	USFAT;	2002/08/29 11:14
and active adj matrix and (organic with (iteld adj effect adj transistor (257/56) or (257/			(257/66) or (257/72) or (257/347) or	EPO; JPO;	
(EL electroluminescence   electroluminescence)   electroluminescence   electroluminesc			(257/350) or (313/512) or (445/25)).CCLS.)		1
electroluminescent)   and gate with (field   adj effect adj transistor FTP bottom adj   gate kop adj gate) and single adj crystal   gate kop adj gate) and single adj crystal   gate kop adj gate) and single adj crystal   gate kop adj gate lop adj gate) and single adj crystal   like lettroluminescence   clectroluminescence   clectrol			and active adj matrix and (organic with	IBM_TDB	1
adj effect adj transistor FRT bottom adj   gate top adj gate op adj gate on ad single adj crystal and (helium he argon ar krypton kr xenon   kr introgen filmert adj   stallea adj get drying)   4 ((1257/57) or (257/59) or (257/66) or (257/737) or (257/56) or (257/72) or (257/347) or (257/59) or (257/347) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.)   DEMMENT: and active adj matrix and organic with (EL electroluminescence clectroluminescence)   EFG. JPO. (257/66) or (257/72) or (257/737) or (257/737) or (257/730) or (313/512) or (445/25)).CCLS.)   DEMMENT:   15M TDB   (1((257/57) or (257/72) or (257/7347) or (257/66) or (257/72) or (257/7347) o		'	'(EL electroluminescence	1	1
gate top adj gato) and single adj crystal and (helium he argon ar krypton kr xenon kentrogen nil) and (helium he argon ar krypton kr xenon xentrogen ninert adj gas rare adj gas) and (barium adj oxide gas rare adj gas) (2577/39) or (313/512) or (2577/39) or (313/512) or (445/25)].ocis.) DERMENT; and active adj matrix and (organic with [EM DE gas rare adj gas to pad] gate land single adj crystal [10 pt] (2577/65) or (2577/77) or (2577/37) or (2577/39) or (313/512) or (445/25)].ocis.) DERMENT; and active adj matrix and (organic with [EM DE gas rare adj gas rare adj gas and (barium he argon ar krypton kr xenon xe nitrogen n [10 pt] (2577/65) or (2577/66) or (2577/65) or (2577/66)	'	1		1	1
and (helium he argon ar krypton kr xenon   xe nitrogen nil) and (helium he argon ar   krypton kr xenon xe nitrogen nil niert adj   gas arae adj gas) and (barium adjoxide   silica adj gal drying)   (257/66) or (257/66) or (257/66) or   (257/76) or		1	gate top adi gate) and single adi grustal	į.	
Re nitrogen nil) and (helium he argon ar krypton kr kenon xe nitrogen ni hert adj gas rare adj gas) and (barium adj oxide silica adj gel drying)   4 (((257/57) or (257/58) or (257/56) or (257/66) or (257/66) or (257/67) or (257/59) or (257/54)) or (257/50) or (257/54) or (257/56) or (257/54) or (257/55) or (257/54)		1	and (helium he argon ar krypton kr xenon	1	
krypton kr xenon xe nitrogen n inert adj gas rare adj gas) and (barium adjoxide silica adj gel drying)	!	1		1	1
gas rare adj gas) and (barium adj oxide silica adj gel drying) 4 '(((257/57) or (257/59) or (257/56) or (257/66) or (257/66) or (257/76) or (257/76) or (257/730) or (257/347) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.)  - (10((257/50) or (257/59) or (257/547) or (257/54) or (257		1		T.	
Silica adj gel drying)   4 (((257/57) or (257/66) or (257/66) or (257/66) or (257/66) or (257/37) or			gas rare adj gas) and (barium adj oxide		
4 (((2577/69) or (2577/59) or (2577/66) or (2577/67) or (2677/67) or (2677/67) or (2677/67) or (2677/67) or (2577/67) or (	!		silica adj gel drying)		1
(257/350) or (313/512) or (445/25)).CCLS.) DERMENT; and active adj matrix and (organic with (EL electroluminoscence clectroluminoscence)   (EL electroluminoscence)   (257/66) or (257/72) or (257/75) or (257/75) or (257/75) or (257/76) or	-	. 4	(((257/57) or (257/59) or (257/66) or		2002/08/29 11:20
and active adj matrix and (organic with IBM TDB (EL electroluminoscence cleetroluminoscence) adj transistor FET bottom adj gate top adj gate) and single adj crystal (1(257/56) or (257/56) or (257/57) or (257/57		1	(257/66) or (257/72) or (257/347) or	EPO; JPO;	1
(EL electroluminoscence					
clectroluminescent) and (field adj offect adj transistor FET bottom adj gate top adj gate) and single adj crystal		1		IBM TDB	1
adj transistor FET bottom adj gate top add gate) and single adj crystal  1 ((((257/57) or (257/59) or (257/66) or USPAT; (257/66) or (257/76) or (257/759) or (257/66) or (257/76) or (257/759) or (257/66) or (257/76) or (257/76) or (257/759) or (257/76) or (257/76) or (257/759) or (257/76) or (313/512) or (445/25)).CCLS.) DERMENT; and active adj matrix and (organic with [KL electroluminescence] and (organic with [KL electroluminescence] and (elium he argon ar krypton kr xeion xe nitrogen n interval gas arac adj gas) and charlum he argon ar krypton kr xeion xe nitrogen n interval gas arac adj gas) and charlum he argon ar krypton kr xeion xe nitrogen n interval gas arac adj gas) and charlum he argon ar krypton kr xeion xe nitrogen n interval gas arac adj gas) and charlum he argon ar krypton kr xeion xe nitrogen n interval gas arac adj gas) and charlum he argon ar krypton kr xeion xe nitrogen n interval gas arac adj gas) and charlum he argon ar krypton kr xeion xe nitrogen n interval gas arac adj gas) and charlum he argon ar krypton kr xeion xe nitrogen n interval gas arac adj gas) and charlum he argon ar krypton kr xeion xe nitrogen n interval gas arac adj gas) and charlum he argon ar krypton kr xeion xe nitrogen n interval gas arac adj gas) and charlum he argon interval gas arac adj gas) and charlum he argon interval gas arac adj gas ara		1			
gate) and single add crystal   1 ((((257)/56) or (257)/69) or (257)/66) or USPAT; (257)/66) or (257)/72 or (257)/347) or EPO; JDO; (257)/350) or (313/512) or (445)/25).CCLS.)   EPO; JDO; (257)/350) or (313/512) or (445)/25).CCLS.)   EPO; JDO; (257)/350) or (313/512) or (445)/25).CCLS.)   EMPKNT; (EL electroluminescence)   and (field add) effect add; transistor FET bottom add) gate top add;   gato) and single add; crystal) and (helium ho argon ar krypton kr xenon xe nitrogen n linet add; gas rare add; gas) and (balium ho argon ar krypton kr xenon xe nitrogen n linet add; gas rare add; gas) and (balium ho argon ar krypton kr xenon xe nitrogen n linet add; gas rare add; gas) and (balium ho argon ar krypton kr xenon xe nitrogen n linet add; gas rare add; gas) and (balium ho argon ar krypton kr xenon xe nitrogen n linet add; gas rare add; gas) and (balium ho argon ar krypton kr xenon xe nitrogen n linet add; gas rare add; gas) (257)/65) or (257)/350) or (257)/350 or (257)/350 or (257)/65) or (257)/650 or (2		1		,	T. T.
1 ((((257/57) or (257/59) or (257/66) or (257/66) or (257/76) or (313/501) cots.) DERWENT; and active adj matrix and (organic with (Et electroluminescence electroluminescence) and (field adj effect adj transistor PET bottom adj gate top adj gate) and single adj crystal) and (helium he argon ar krypton kr xenon xe nitrogen n inert adj gas rare adj gas) and charlum adj (257/66) or (257/72) or (257/73) or (257/766) or (257/72) or (257/73) or (257/766) or (257/72) or (257/73) or (257/765) or (257/72) or (257/73) or (257/73) or (257/76) or (257/72) or (257/73) or (257/73) or (257/74) or (257/				1	1
(2577/66) or (2577/2) or (257/347) or   EPO; JDO;   (2577/350) or (313/512) or (445/25).CCLS.)   EDEMENT;   and active adj matrix and (organic with   IBM TDB   (EL electroluminescence   electrolum	_	1		TICOMT.	2002/08/29 11:15
(257/350) or (313/512) or (344/25)).CCLS.)   DERWENT; and active adj matrix and (organic with   IBM TDB   (EL electroluminescence   electroluminescence   electroluminescence   adj transistor FET bottom adj gate top adj   gato) and single adj crystai) and (helium   he argon ar kryptom kr xemon xe nitrogen n   inert adj gas rare adj gas) and (balium   adj exide silica adj ged drying)   USPAT;   2003/06/12 14:12   270; JPO;   270; JPO; JPO;   270; JPO;   270; JPO;   270; JPO;   270; JPO;   270; JPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO					2002/00/25 #1.15
and active adj matrix and (organic with [BM TDB   (KL electroluminescence electroluminescence)   and (field adj effect   adj transistor FET bottom adj gate top adj   gato) and single adj crystal ) and (helium   he argon ar kryptom kr xenon xe nitrogen n   linet adj gas rare adj gas) and (balium   adj oxide silica adj ged drying)   (1(257/55) or (257/759) or (257/66) or [257/66) or (257/759) or (257/766) or [257/759] or (257/766) or [257/759] or (257/766) or [257/759] or (257/759) or (257/766) or [257/759] or (257/766) or [257/759] or (257/766) or [257/759] or (257/759] or (257/766) or [275/746] o		1			
(EL electroluminescence electroluminescence) and (field adj effect adj transistor PET bottom adj gate top adj gate) and single adj crystai) and (helium he argon ar kryptom kr xenon xe nitrogen n inert adj gas rare adj gas) and (balium adj oxide silica adj gas) and (balium adj oxide silica adj gel drying)  - (1257/590 (1237/59) (1257/68) or (		1			
electroluminescent) and (field adj effect   adj transistor PET bottom adj gate top adj   gato) and single adj crystal ) and (helium   he argon ar kryptom kr xenon xe nitrogen n   linet adj gas rare adj gas) and (balium   adj oxide silica adj ged drying)   uspar;   2003/06/12 14:12   (1(257/55) or (257/759) or (257/66) or   Uspar;   2003/06/12 14:12   (1257/65) or (257/759) or (257/66) or   Uspar;   2003/06/12 14:12   (1257/65) or (257/759) or (257/66) or   Uspar;   2003/06/12 14:12   (1257/65) or (257/759) or (257/66) or   Uspar;   and matrix and (organic with (EL   clectroluminescence electroluminescent)   nad (field adj effoct adj transistor PET   bottom adj gate top adj gate) and single   uspar;   uspar;   uspar;   uspar;   uspar;   uspar;   uspar;   2002/08/29 11:58   uspar;   u		1	(EL electroluminescence		100
gato) and single adj crystal ) and (helium hargon ar Krypton Kr xenon xe nitrogen n linet adj gas rare adj gas) and (barium adj oxide silica adj ged drying)   1		1	electroluminescent)) and (field adj effect	1	
gato) and single adj crystal ) and (helium hargon ar Krypton Kr xenon xe nitrogen n linet adj gas rare adj gas) and (barium adj oxide silica adj ged drying)   1		1	adj transistor FET bottom adj gate top adj	1	!
Inert adj gas Farc adj gas) and (bartum adj oxide silica adj gel drying)		1	'gate) and single adj crystal ) and (helium	1	
adj oxide silica adj gel drying)   4 (((251/57) or (257/56) or (257/56) or (257/56) or (257/56) or (257/347) or (257/347		:			1
- 4 (((25)/59) or (25)/59) or (25)/69) or (313/512) or (345/29)].CCLS.) DERWENT; DERWEN			inert adj gas rarc adj gas) and (barium		1
(257/66) or (257/72) or (757/347) or   ZPO; JPO;   C257/350) or (313/512)   CCLS.)   EDEMENT;   IMM_TDB   Colectroluminescence electroluminescent)   and (field adj effoct adj transistor FET   bottom adj gate top adj gato) and single   adj crystal   USPAT;   USPA			adj oxide silica adj gel drying)	Lucasa	1 2000 (05 (10 14 10
(257/350) or (313/512) or (344/25)).CCLS.)   DERMENT; and matrix and (organic with (EL clectroluminescence electroluminescent)   IHM_TDB	_	. "	(((25//5/) Or (25//59) Or (25//66) Or		2003/06/12 14:12
and matrix and (organic with (EL cleetroluminescent)) and (field adj effoct adj transistor FET bottom adj gate top adj gate) and single adj crystal USPAT; US-PCPUB; EPG; JFO; JFO; DERMENT; IBM TDB USPAT; U					
Clectroluminescence electroluminescent)   and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal   USPAT;   US-RCPUB;   EPG; JBO;   DERMENT;   LBM TDB   USPAT;		1			
and (field adj effoct adj transistor FET bottom adj gate top adj gate) and single adj crystal  - 1075 313/504  - 0 313/504  - 0 313/504,500  - 1650 313/504 313/500  - 1650 313/504 313/500  - 1650 313/504 313/500  - 1650 313/504 313/500  - 1650 313/504 313/500  - 175 313/504  - 1064 ((313/504) or (313/500)).CCLS.) AND  - 1064 ((313/504) or (313/500)).CCLS.) AND  - 116 (((313/504) or (313/500)).CCLS.) AND  - 116 (((313/504) or (313/500)).CCLS.) AND  - 116 ((((313/504) or (313/500)).CCLS.) AND  - 116 ((((313/504) or (313/500)).CCLS.) AND  - 116 (((((313/504) or (313/500)).CCLS.) AND  - 116 (((((((313/504) or (313/500)).CCLS.) AND  - 116 ((((((((((((((((((((((((((((((((((		1		1111_100	
bottom adj gate top adj gate) and single adj crystal   USPAT;   US-RCPUB;   EPO; JPO;   DERMENT;   LINE TOB   USPAT;   US-RCPUB;   EPO; JPO;   DERMENT;   LINE TOB   USPAT;   US-RCPUB;   EPO; JPO;   DERMENT;   LINE TOB   USPAT;   US-RCPUB;   USPAT;   USP		1			1
- 1075 313/504 USPAT; U		1	bottom add gate top add gate) and single		
- 1075 313/504 USPAT; 2002/08/29 11:58 USPAT; 2002/08/29 12:20 USPAT; 2002/08/29 12:20 USPAT; 2002/08/29 12:21 USPAT; 2002/08/29 12:21 USPAT; 2002/08/29 12:36 USPAT; 2002/08/29 12:21 USPAT; 2002/08/29 12:23 USPAT; 2002/08/29 13:32 USPAT; 2002/08/			'adj crystal		
- 0 313/504,500	-	1075	313/504	USPAT;	2002/08/29 11:58
- 0 313/504,500   1BM TDB   USPAT;   2002/08/29 11:58   USPAT;   2002/08/29 11:58   USPAT;   2002/08/29 12:20   USPAT;   2002/08/29 12:20   USPAT;   2002/08/29 12:21   USPAT;   2002/08/29 12:23   USPAT;   2002/08/29 13:32   US		1	T. Control of the Con		
- 0 313/504,500			1		
- 0 313/504,500			t.		
- 1650 313/504 313/500		1	202/504 500		
- 1650 313/504 313/500	-	, ,	3137504,500		5008/08/89 11:28
- 1075 313/504 . US-RCPUB . US-PCPUB . EPG, JPG. DERMENT: . IN TOB . USPAT: . EPG, JPG. DERMENT: . IN TOB . EPG, JPG. DERMENT: . IN TOB . EPG, JPG. DERMENT: . EPG,	_	1.650	313/504 313/500		2002/09/29 12:20 1
- 1075 313/504 USPAT; 2002/08/29 12:21 USPAT; 2002/08/29 12:21 USPAT; 2002/08/29 12:21 USPAT; 2002/08/29 12:21 USPAT; 2002/08/29 12:36 USPAT; 2002/08/29 12:21 USPAT; 2002/08/29 12:23 USPAT; 2002/08/29 12:24 USPAT; 2002/08/29 USPAT; 2002/08/		1 000	010,001 010,000		. 2002/00/25 12:20
- 1064 ((313/504) or (313/500)).CCLS. USPAT:	_	1075	1313/504		2002/08/29 12:21
- 1064 ((313/504) or (313/500)).CCLS. USPAT; 2002/08/29 12:36 US-MCPUB; EPG; JPG; DERMENN; IDM TOB SERVED TO SERVED					
US-NEQUE; EPO; JPO; DERMENT; INB TOB Active adj matrix  - 114 ((((313/504) or (313/500)).CCLS.) AND USPĀT; Active adj matrix - 114 (((((313/504) or (313/500)).CCLS.) AND USPĀT; Active adj matrix) and (field effect US-NEQUE); transistor fet) - 9 (((((313/504) or (313/500)).CCLS.) AND USPĀT;   IRM TOB USPĀT;   EPO; JPO;   DERMENT;   IRM TOB USPĀT;   POS POPUB;   Cattive adj matrix) and (field effect US-NEQUE);   IRM TOB USPĀT;   EPO; JPO;   DERMENT;   EPO; JPO;   DERMENT;   EPO; JPO;   DERMENT;	-	1064	'((313/504) or (313/500)).CCLS.		2002/08/29 12:36.
EPG; JPO; DEFMENT; IDN TOB SPAT; 2002/08/29 12:21 SPAT; 2002/08/29 12:23 SPAT; 2002/08/29		1	T		
TIM TOB		1	f.	EPO; JPO;	
- 116 (((313/504) or (313/500)).CCLS.) AND USPĀT; 2002/08/29 12:21  - Active adj matrix			1		
Active adj matrix		1	*		
- 114 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 12:23   - 124 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 12:23   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 (((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 13:32   - 125 (((((((((((((((((((((((((((((((((((	-	116			2002/08/29 12:21
- 114 ((((313/504) or (313/500)).CCLS.) AND USPÄT; Active add matrix) and (field effect US-FOPUB; transistor fet) FPO; JPO;   (((((313/504) or (313/500)).CCLS.) AND USPÄT;   (IIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIII			Active adj matrix		
- 114 (((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 12:23 USPÄT; USP		1	1		1
- 114 ((((313/504) or (313/500)).CCLS.) AND USPÄT; 2002/08/29 12:23 USPÄC; 2002/08/29 USPÄC; 200		T.			1
Active adj matrix) and (field effect US-PGPUB; transistor fet) FDC; JPO; DERMENT; IRM TOB USPAT; IRM TOB USPAT; Active adj matrix) and (field effect US-PGPUB; transistor fet)) and single adj crystal EPO; JPO; DERMENT; EPO; JPO; DERMENT; Active adj matrix) and field effect US-PGPUB; Transistor fet) and single adj crystal EPO; JPO; DERMENT; DERMENT;	-	114	1 ((((313/504) or (313/500)) ccts ) AND		2002/08/29 12:22
transistor fet		. 114			2002/00/29 17:23
DERMENT;   I.M. TUB   (((((313/504) or (313/500)).CCLS.) AND					
IEM TDB		T	/		
9 (((((313/504) or (313/500)).CCLS.) AND USPĀT; 2002/08/29 13:32     Active adj matrix) and (field effect USPGPUB; EPO; JPO; transistor fet)) and single adj crystal EFO; JPO; DEKMENT;		ļ.			
Active adj matrix) and (field effect US-PGPUB; transistor fel)) and single adj crystal EFO; PFO; DERMENT;	-	, 9	((((((313/504) or (313/500)).CCLS.) AND		2002/08/29 13:32
DERWENT;			Active adj matrix) and (field effect		
			transistor fet)) and single adj crystal		1
TBM_TDB		1			
			les de les de la	IBM_TDB	

1 -	,	7 [ (((((313/504) or (313/500)).ccrs.) AND -	USPAT;	72002/08/29	12:28 1
1	1	Active adj matrix) and (field effect	US-PGPUB:	i	
1	1	transistor (et)) and single adj crystal)	EPO; JPO;		
	1	, and (inert adj gas rare adj gas helium he	DERWENT;		,
i .	1	krypton kr argon ar xenon xe nitrogen n)	IBM TOB	1	1
1 -	1	7 (((((((313/504) or (313/500)).CCLS.) AND	USPAT;	2002/08/29	12:36:
i	Ť	'Active adj matrix) and (field effect	US-PGPUB;		1
	1	transistor fet)) and single adj crystal)	EPO; JPO;		
		, and (inert adj gas rare adj gas helium he	DERWENT;		
1	1	krypton kr argon ar xenon xe nitrogen n)	IBM TOB	1	7
1 -	1	0 20020074938.URPN.	USPAT	12002/08/29	12:35;
1 -	1	810 (((313/504) or (313/500)).CCLS.) and	USPAT;	2002/08/29	12:37
		(inert adj gas narc adj gas helium he	US-PGPUB;		1
,		krypton kr argon ar xenon xe nitrogen n)	EPO; JPO;	1	
1	;		DERWENT;	1	
1	1		IBM TDB	1	
, -	1	530 (((313/504) or (313/500)).CCLS.) and	USPAT;	2002/08/29	12:38
	1	' (inert adj gas rare adj gas helium he	US-PGPUB;		
,	1	krypton kr argon ar xenon xe nitrogen n)	LEPO; JPO;	1	1
1		and (organic ad; EL organic ad; layer)	DERWENT;	1	
			IBM TDB		
, -	,	407 (((313/504) or (313/500)).CCLS.) and	USPAT;	2002/08/29	12:39 1
	1	(inert adj gas rare ad) gas helium he	US-PGPUB;	T.	1
	1	krypton kr argon ar xenon xe nitrogen) and	EPO; JPO;		
4	1	(organic adj EL organic adj layer)	DERWENT;	1	- 1
1			IBM TDB		1
· -	į.	2 (((313/504) or (313/500)).CCLS.) and	USPAT;	2002/08/29	12:40
1	1	'(inert adj gas rare adj gas helium he	US-PGPUB;	î .	
1	1	krypton kr argon ar xonon xe nitrogen)	EPO; JPO;	ī	1
1		same (envelope vacant vacancy) and	· DERWENT;	1	1
		(organic adj EL organic adj layer)	TBM TDB		1
· -		181 (((313/504) or (313/500)).CCLS.) and	USPAT;	12002/08/29	12:41 .
1	1	(inert adj gas rare adj gas helium he	US-PGPUB;	Y	1
1	1	krypton kr argon ar xenon xe nitrogen) and	EPO; JPO;	1	1
		(organic adj EL organic adj layer) and	DERWENT;		
. 1		(barium adj oxide silica gel)	IBM TDB	1.	7
-		57 (((313/504) or (313/500)).CCLS.) and	USPAT;	1 2002/08/29	12:44
'	1	(inert adj gas rare adj gas helium he	· US-PGPUB;	:	
1		<ul><li>krypton kr argon ar xenon xe nitrogen)</li></ul>	· EPO; JPO;	1	
,	1	same (barium adj oxide silica gel) and	, DERWENT;		
		(organic adj EL organic adj layer)	, FBM TDB		1
1 -		615 (((313/504) or (313/500)).CCLS.) and	USPAT;	2002/08/29	12:44
		(organic adj EL organic adj layer)	US-PGPUB;	1	
		'	EPO; JPO;	1	
1		· ·	DERWENT;		
1			, IBM_TDB	1	1
	1	57 (((((313/504) or (313/500)).CCLS.) and	USPAT;	2002/08/29	12:45:
1		(organic adj EL organic adj layer) ) and	US-PGPUB;	*	1
	1	(inert adj gas rare adj gas helium he	'EPO; JPO;	1	
1	1	krypton kr argon ar xenon xe nitrogen)	DERWENT;	1	,
	1	same (barium ad) oxide silica gel)	· IBM_TDB		
-		57 ((((313/504) or (313/500)).CCLS.) and	, USPAT;	2002/08/29	12:47
		(organic adj EL organic adj layer) ) and	US-PGPUB;		- 1
1	1	(inert adj gas rare adj gas helium he	EPO; JPO;	,	
	7	krypton kr argon ar xenon xe nitrogen)	DERWENT;	1	
		same (barium ad; oxide silica gel)	IBM_TDB	:	1
-		48 ((((313/504) or (313/500)).CCLS.) and	. USPĀT;	2002/08/29	13:33
		'(organic adj EL organic adj layer) ) and	US-PGPUB;		1
		'(inert ad) gas rare ad) gas helium he	EPO; JPO;		1
1		krypton kr argon ar xenon xe nitrogen)	DERWENT;		
	1	same (barium adj oxide silica adj gel)	IBM_TDB	1	
' -		10 (((((313/504) or (313/500)).CCLS.) AND	USPAT;	' 2002/08/29	13:32
		Active adj matrix) and (field effect	US-PGPUB:	1	
1	1	transistor (et)) and (single adj crystal	EPO; JPO;		i i
	1	monocrystal monocrystalline)	DERWENT;		
0.6			IBM_TDB	ed in	:

( =	7	0 ((((((313/504) or (313/500)).ccts.) AND	USPĀT;	2002/08/29 13:53
1	1		US-PGPUB;	1
			EPO; JPO;	1
	1	monocrystal monocrystalline)) and (inert	DERWENT;	1
,	1	adj gas rare adj gas helium he krypton kr	IBM_TDB	1
1	1.0	argon ar xenon xe nitrogen) same (barium adj oxido silica adj gel)		,
! _	1	3 (((((313/504) or (313/500)).CCLS.) AND	USPAT;	2002/08/29 13:54
2		Active adj matrix) and (field effect	US-PGPUB;	17.002,00727 13.51
		transistor fet)) and (inert adj gas rare	EPO; JPO;	
1			DERWENT;	
1	- 1	xenon xe nitrogen) same (barium adj oxide	IBM TDB	
	i	silica adj gel)	1	1
			. USPAT;	, 2002/08/29 13:57
	1	(257/66) or (257/72) or (257/347) or	US-PGPUB;	ř t
		(257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.	EPO; JPO;	1 2
		(313/300) Of (313/304) Of (313/493)).CCBS.	DERWENT; IBM TDB	
1		0 (((257/57) or (257/59) or (257/66) or	USPAT;	2002/08/29 14:00
			US-PGPUB;	1 2002/00/25 14.00
			EPO; JPO;	1
	1	(313/500) or (313/504) or	DERWENT;	
		(313/495)).CCLS.) and active adj matrix	IBM TDB	
	,	and (FET field adj effect adj transistor)		No.
	1	same organic adj EL and (barium adj oxide	t .	1
	1	silica gel) and (helium he nitrogen	l .	
1		krypton kr argon ar xenon xe)		
	1	1 (((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or	USPAT; US-PGPUB;	2002/08/29 14:01
1		(257/350) or (313/512) or (445/25) or	EPO; JPO;	
1		(313/500) or (313/504) or	DERWENT;	r
1		(313/495)).CCLS.) and active adj matrix	IBM TDB	1 1
ī		and (FET field adj effect adj transistor)		i .
į.		and organic adj EL and (barium adj oxide	î .	
1		'silica adj gel) and (helium he nitrogen		
1		(krypton kr argon ar xenon xe)		
-		1 (((257/57) or (257/59) or (257/66) or	USPAT;	12002/08/29 14:03!
1			US-PGPUB;	1
1			EPO; JPO;	1
1		(313/495)).CCLS.) and active adj matrix	DERWENT;	
1		and (FET field adj effect adj transistor)	. 100_100	1
		and organic with (EL electroluminescent		
1		electroluminescence) and (barium adj oxide		
:	1	'silica adj gel) and (helium he nitrogen		
		'krypton kr argon ar xenon xe)		
		1 (((257/57) or (257/59) or (257/66) or	USPAT;	. 2002/08/29 14:03
T	191	(257/66) or (257/72) or (257/347) or	US-PGPUB;	
1	1	(257/350) or (313/512) or (445/25) or (313/500) or (313/504) or	EPO; JPO; DERWENT;	
1			· IBM TDB	4
1		and (FET field adj effect adj transistor)	- 51 255	'
1		and organic and (EL electroluminescent		
		'electroluminescence) and (barium adj oxide		8- 1
		'silica adj gel) and (helium he nitrogen		
		krypton kr argon ar xenon xe)	-	1
, -			. USPAT;	2002/08/29 14:23
1			US-PGPUB	1
		(257/350) or (313/512) or (445/25) or (313/500) or (313/504) or		
	7	(313/300) of (313/304) or (313/495)).CCLS.) and active adj matrix	<u>t</u>	
		and (FET field adj effect adj transistor)		
1	1	and organic and (EL electroluminescent		
1	1	electroluminescence) and (barium adj oxide		
		silica adj gel) and (helium he nitrogen		i i
ı	4	, krypton kr argon ar xenon xe)		
		2 , ("6175186").PN.	USPAT;	2002/08/29 14:04
			US-PGPUB;	
	- 1		'EPO; JPO; DERWENT;	
	1		IBM TDB	
			TOM IND	

24 ((257/57) or (257/59) or (257/66) (257/66) or (257/72) or (257/347) o	or USPAT; r US-PGPUB;	2002708/29	14:06
(257/350) or (313/512) or (445/25)	or FPO; JPO;	1	
(313/500) or (313/504) or	DERWENT;	1	
(313/495)).CCLS.) and active adj ma and (FET field adj effect adj trans	trix TBM_TDB	V.	1
and organic and (E) electroluminesc		1	
electroluminescence) and (holium he			
nitrogen krypton kr argon ar xenon : 10 (((257/57) or (257/59) or (257/66)	xe) or USPAT;	2002/08/29	14:27
(257/66) or (257/72) or (257/347) o			
(257/350) or (313/512) or (445/25)	or EPO; JPO;	1	
(313/500) or (313/504) or (313/495)).CCLS.) and active adj ma	DERWENT; trix IBM TDB	î	1
'and (FET field adj effect adj trans	istor)	1	,
and organic with (EL electrolumines	cent		
electroluminescence) and (helium he mitrogen krypton kr argon ar xenon :	vol :	1	
1 (((257/57) or (257/59) or (257/66)	or USPAT;	12002/08/29	14:35.
(257/66) or (257/72) or (257/347) o	r US-PGPUB;	T.	1
(257/350) or (313/512) or (445/25) (313/500) or (313/504) or	or 'EPO; JPO; DERWENT;		- 1
(313/300) Of (313/304) Of (313/304) Ma			
and (FKT field ad) effect ad) trans	istor)	1	1
and organic with (EI, electrolumines	cent '	1	- 1
electroluminescence) and (helium he nitrogen krypton kr argon ar xenon:	xc) and		i
goggle			- 1
1 (((257/57) or (257/59) or (257/66)		2002/08/29	14:23
(257/66) or (257/72) or (257/347) o (257/350) or (313/512) or (445/25)		1	ī
(313/500) or (313/504) or			
(313/495)).CCLS.) and active adj ma			1
and (FET field ad) effect adj trans and organic and (EL electroluminese		1	
electroluminescence) and (barium ad		1	1
'silica adj gel)		1	
1; jp10285476 15; (((257/57) or (257/59) or (257/66)	JPO or USPAT;	2002/08/29	
(257/66) or (257/72) or (257/347) o		, 2002/00/29	13.33
(257/350) or (313/512) or (445/25)	or EPO; JPO;	1	1
(313/500) or (313/504) or (313/495)).CCLS.) and active adj ma	trix DERWENT;		1.5
and (FET field adj effect adj trans			
and organic with (EL electrolumines			
: electroluminescence)	Hanne	12002/08/29	14.20
537, (((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) o		2002/08/29	14:36
(257/350) or (313/512) or (445/25)		i	
(313/500) or (313/504) or	DERWENT;		- 1
(313/495)).CCLS.) and organic with clectroluminescent electroluminesce.	(EL IBM_TDB		- 1
and (helium he nitrogen krypton kr	argon		1
ar xenon xe) and (barium oxido sili	ca adj .	į.	- 1
gel) 11 (((257/57) or (257/59) or (257/66)	or 'USPAT;	2002/08/29	14.41
(257/66) or (257/72) or (257/347) o	r EPO; JPO;	, 2002/05/25	14.41
(257/350) or (313/512) or (445/25)	or DERWENT;	1	- 1
(313/500) or (313/504) or (313/495)).CCLS.) and organic with	, IBM_TDB	4	1
electroluminescent electroluminescen		1	
and (helium he nitrogen krypton kr	argon '	i.	1
ar xenon xe) and (barium oxide sili-	ca adj '		
gel) and goggle 0 jpl0333665 0 semiconductor adi laboratory and va	JPO	2002/08/29	14:42
		2002/08/29	
and "1998"			
5179 yamazaki and "1998" 0 yamazaki and "1998" and semiconduct	JPO oradj JPO	2002/08/29	
energy adj laboratory	or auj JEO		14.42.
0 '10-333665 and yamazaki	JPO	2002/08/29	14:48
The section of the se			

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- 17	0 '	"1333665" and yamazaki "10333665" and yamazaki	JPO JPO	12002/08/29	
1	0 1				
1		#1-10333666# d		, 2002/08/29	
1	0 .	"jp10333665" and yamazaki "jp410333665" and yamazaki	, JPO	2002/08/29	14:48
	0 1	"jp310333665" and yamazaki	JPO JPO	1 2002/08/29	14:40
1	0 '	"jp310333665"	JPO	, 2002/08/29	
1	0 :	"jp410333665"	. JPO	2002/08/29	
1	0	"jp10333665"	JPO	2002/08/29	
1	368	(((257/57) or (257/59) or (257/66) or	USPAT;	2002/08/29	14:50
		(257/66) or (257/72) or (257/347) or	EPO; JPO;		
,	,	(257/350) or (313/512) or (445/25) or			
			TBM_TDB	1	
				1	1
			i .	1	
!	,		i		i
	1	gel)		1	1
1	83 1	(((257/57) or (257/59) or (257/66) or	USPAT;	2002/08/29	14:51.
1	- 1	(257/66) or (257/72) or (257/347) or	EPO; JPO;	1	,
1	- 1	(257/350) or (313/512) or (445/25) or	. DERWENT;	T	- 1
1			IBM TDB	I .	
		(313/495)).CCLS.) and organic with (EL			
1	1	electroluminescent electroluminescence)			
1	1		I .	1	
				1	- 1
,			. Henry.	2002/00/20	14.52
,	30 1			2002/00/29	14:32
1	i	(257/350) or (313/512) or (445/25) or		1	
1		(313/500) or (313/504) or			- 1
			1200_100		1
	,			100	
	1	and (helium he nitrogen krypton kr argon	1	1	1
	- 1	ar xenon xe) same (barium ad) oxide silica	1		1
	- 1	adj gel)		•	1
1	3	(((257/57) or (257/59) or (257/66) or		2002/08/29	14:55
		(257/66) or (257/72) or (257/347) or			1
1	,	(257/350) or (313/512) or (445/25) or			1
,			TRW_LDR		1
				1	
				1	,
	- 1		1	1	,
	7 '	("5739545"   "5747930"   "5834894"	HSPAT	2002/08/29	14.54
		"6037718"   "6046543"   "6246179"			1
	1	"6307324").PN.			1
			USPAT;	2002/08/29	15:13
			US-PGPUB;		
			EPO; JPO;		1
			IBM TDB		
	0	(313/\$ and ceramic with transparent).CCLS.		2002/08/29	15:27
					,
	1			1	-
			TRM TOR		1
	0.1	(313/S and ceramic same transparent) CCIS	IISDATION	2002/08/29	15.27 .
	٠,	(515) 4 and ceramic name clamparette, cons.		, 2002/00/7,3	13.21.
			DERWENT;		
	1		IBM TDB	1	
	0 .	(313/\$ and ceramic same clear).CCLS.	USPAT;	12002/08/29	15:27 '
	1		. US-PGPUB;	I .	1
	1		EPO; JPO;	1	1
			DERWENT;	i	- 1
		(824.28)	TBM_TDB		
1	00900			, 2002/08/29	15:27 (
1				I .	- 1
1	i			1	1
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History		/13/03 1:42:57 PM Page 11			'
		368	368 (((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495). CCIS.) and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xo) and (barium oxide silica add gel) (257/66) or (257/72) or (257/66) or (257/350) or (313/504) or (313/495). CCIS.) and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xo) and (barium adj oxide silica electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xo) and (barium adj oxide silica adj gel) (((257/55)) or (257/59) or (257/66) or (257/66) or (257/50) or (313/504) or (313	368 (((257/57) or (257/59) or (257/66) or (257/57) or (257/59) or (257/59) or (257/59) or (257/59) or (257/59) or (257/59) or (313/495)).CCLS.) and organic with (EL electroluminescent clectroluminescent clectroluminescent (257/66) or (257/57) or (257/59) or (257/66) or (257/69) or (313/500) or (	368 (((257/57) or (257/59) or (257/66) or (257/66) or (257/66) or (257/65) or (313/501) or (313/501) or (345/25) or (345/25) or (313/501) or (345/25)

	× r	0.5	((313/\$).CCLS.) and nitride adj ceramic	USPAT;	2002/08/29 15	1.28
			with (clear transparent transparency)	US-PGPUB;	1 2002/00/15 10	1
			with (clear clanaparent commaparency)	EPO; JPO;	1	1
		1			1	
				DERWENT; JBM TDB	1	,
	' '	ra I			1 0000 (00 (00 1	
-	. 3	159	((313/\$).CCLS.) and ceramic with (clear	USPAT;	2002/08/29 16	5:50
	1		transparent transparency)	US-PGPUB;	1	
		1		EPO; JPO;	I .	1
	1			DERWENT;		
				IBM TDB		
~		0 ,	(((257/57) or (257/59) or (257/66) or	USPAT	1 2002/08/29 15	5:54
			(257/66) or (257/72) or (257/347) or			
	1		(257/350) or (313/512) or (445/25) or			
	1		(313/500) or (313/504) or	1	1	,
	į.		(313/495)).CCLS.) and active adj matrix			1
			with goggle		7	
-	1		(((257/57) or (257/59) or (257/66) or	USPAT	2002/08/29 15	
			(257/66) or (257/72) or (257/347) or	OSTAL	2002/00/23 1.	,,,,,
	,	1	(257/06) 01 (257/12) 01 (257/147) 01	1	1	
			(257/350) or (313/512) or (445/25) or		1	Ÿ
	1		(313/500) or (313/504) or	1		
	1		(313/495)).CCLS.) and display with goggle	1	1	- 1
-	1		jp10361563	JPO	2002/08/29 15	
-	1	0	jp010361563 (((257/57) or (257/59) or (257/66) or	1 JPO	2002/08/29 15	5:58
-		2.5 '	(((257/57) or (257/59) or (257/66) or	USPAT	2002/08/29 15	5:59 '
	1		(257/66) or (257/72) or (257/347) or			- 1
	1		(257/350) or (313/512) or (445/25) or			
	1		(313/500) or (313/504) or	1	1	
			(313/495)).CCLS.) and display same goggle		1	- 1
_	1	26	(((257/57) or (257/59) or (257/66) or	USPAT	: 2002/08/29 16	. 16 .
	1		(257/66) or (257/72) or (257/347) or	USERI	1 2002/00/29 10	1.40
				1	I .	
			(257/350) or (313/512) or (445/25) or		1	
	Ī	1	(313/500) or (313/504) or			- 1
	1	- 1	(313/495)).CCLS.) and display and goggle		T	
-		9 '	nitride adj ceramic with (transparent	USPAT	2002/08/29 16	5:47
	1		clear)	1		1
-	1		nitride adj ceramic with oxide with glass	. USPAT	2002/08/29 16	5:47
	1		with (transparent clear)		1	- 1
-		28	((313/\$).CCLS.) and nitride adj ceramic	USPAT;	2002/08/29 10	5:52 -
			·	US-PGPUB;		
		1		'EPO; JPO;	1	
	1	- 1		DERWENT;	f .	,
		- 1		JBM TDB		- 1
		0 '	((313/\$).CCLS.) and nitride adj ceramic	USPAT;	2002/08/29 16	
		0			1 2002/00/29 1	0:01.
			same (transparent clear)	US-PGPUB;	1	
				EPO; JPO;		
				DERWENT;		
		1		IBM TOB		
-	1		((313/\$).CCLS.) and nitride with ceramic	USPAT;	. 2002/08/29 1	7:07 '
			same (display clear transparent	· US-PGPUB;		
			transparency)	EPO; JPO;		
				DERWENT;		1
				IBM TDB	Y	
-		0.1	ip102854476	: JPO	2002/08/29 13	1:07
_			jp12854476	, JPO	2002/08/29 13	
_	1		1p0102854476	, JPO	2002/08/29 1	1.12
_			("6351010").PN.			
		21	( 0301010 ).EN.	USPAT;	2002/08/29 17	1113
				US-PGPUB;	1	
				EPO; JPO;	1	
	4	- 1		DERWENT;		
	1			1BM_TDB		
-	1	0	("1459 and yamanaka and insulated adj	USPAT;	2002/08/29 17	7:13
			gate").PN.	US-PGPUB;	1	
				EPO; JPO;	1	i
	7	1		DERWENT;		
				TBM TDB		
-		8 .	(((257/57) or (257/59) or (257/66) or	USPAT;	2002/08/29 17	16
		X	(257/66) or (257/12) or (257/347) or	US-PGPUB;	1	
			(257/350) or (313/512) or (445/25) or	EPO; JPO;		Ť.
			(313/500) or (313/504) or	DERWENT;		1
		7				
			(313/495)).CCLS.) and yamanaka and	IBM_TDB	1	
			insulated adj gate		I was a second	"

(257/66) or (257/72) or (257/37) or   US-PGFUB;   (257/35) or (313/512) or (445/24) or   PEO, JBO;   (313/500) or (313/512) or (445/24) or   PEO, JBO;   (313/495)). Cold.; ) and insulated adj gate adj field   USPAT;   2002/08/29 17:18   and organic   US-PGFUB;   EPO, JBO;   DERWENT;   EPO, JBO;   EP		0	(((257/57) or (257/59) or (257/66) or	USPAT;	2002/08/29 17:17
(257/350) or (313/502) or (445/25) or   RPO; JPO;   (313/503) or (313/505) or (31					, 2002/00/25 17:17
(313/595) or (313/504) or (313/505) or (313/507) or (31	4	1			
(313/495)).CCLS.) and insulated adj gate   IBM_TDB   and organic adj layer   USPAT;   2002/08/29 17:18   and organic   USPAT;	1		(257/350) or (313/512) or (445/25) or	EPO; JPO;	
(313/495)).CCLS.) and insulated adj gate   IBM_TDB   and organic adj layer   USPAT;   2002/08/29 17:18   and organic   USPAT;			(313/500) or (313/504) or	DERWENT:	1
and organic adj layer and organic and organic and organic and organic and organic and organic  389 yamazaki-shunpei.in. or arai-yasuyuki.in. 29 yamazaki-shunpei.in. and arai-yasuyuki.in. 210 yamazaki-shunpei.in. and arai-yasuyuki.in. 389 yamazaki-shunpei.in. and arai-yasuyuki.in. 389 yamazaki-shunpei.in. and arai-yasuyuki.in. 380 yamazaki-shunpei.in. a					in the second se
3   sony.as. and insulated adj gate adj field   USPAT;   SPGCUB;   and organic   USPAT;   U	1	7	(313/433)/.cc/33.) and insuraced adj gate	, IBM_LDB	1
and organic	1				
SEO, JPC;   DERRENT;   IRM TDB   2003/06/11 18:07   2003/06/11 18:07   2003/06/11 18:07   2003/06/11 18:07   2003/06/11 18:07   2003/06/12 11:07	-	1 3	sony.as. and insulated adj gate adj field	USPAT;	2002/08/29 17:18 ,
SEO, JPC;   DERRENT;   IRM TDB   2003/06/11 18:07   2003/06/11 18:07   2003/06/11 18:07   2003/06/11 18:07   2003/06/11 18:07   2003/06/12 11:07	1		and organic	: IIS-PGPUR:	1
DERMENT:   IMM TOB   2003/06/11 18:07   2003/06/11 18:07   2003/06/11 18:07   2003/06/11 18:07   2003/06/11 18:07   2003/06/11 18:07   2003/06/11 18:07   2003/06/11 18:07   2003/06/11 18:07   2003/06/11 18:07   2003/06/11 18:07   2003/06/12 11:17   2003/06/12 11:17   2003/06/12 11:17   2003/06/12 11:17   2003/06/12 11:17   2003/06/12 11:17   2003/06/12 11:01   2003/06/1					1
S89   yamazaki-shunpei.in. or arai-yasuyuki.in.   S=GFUB   2003/06/11 18:07		1			1
389   yamazaki-shumpei.in. or arai-yasuyuki.in.   US-GCUD   2003/06/11 18:07   21   yamazaki-shumpei.in. and arai-yasuyuki.in.   US-FGUD   2003/06/12 11:17   and organic   US-FGUD   2003/06/12 11:17   and organic   US-FGUD	1		1		
22   yamazaki-shunpei.in. and arai-yasuyuki.in.   US-FOFUB   2003/06/12 11:17		1		IBM TDB	
22   yamazaki-shunpei.in. and arai-yasuyuki.in.   US-FOFUB   2003/06/12 11:17	1	1 389	vamazaki-shunpei.in. or arai-vasuvuki.in.	US-PGPUB	2003/06/11 18:07
21   yamazaki-shunpei.in. and arai-yasuyuki.in.   US-RQFUB   2003/06/12 11:17   and organic   9   "passivation film 847"   US-RQFUB   EPG; JPG; DEFMENT; IBM TOB   USPAT; USPAT	1 -				
and organic  9 "passivation film 847"  0 "passivation film 847 is formed on the anode layer 846"  - 0 "passivation film 847 is formed on the anode layer 846"  - 0 "passivation film 847 is formed on the anode layer 846."  - 0 "passivation film 847 is formed on the anode layer 846."  - 1420 semiconductor adj device adj method adj tabricating  - 1420 semiconductor adj device adj method adj tabricating  - 745 semiconductor adj device adj method adj tabricating t					
9	, -	, 21	, yamazaki-shunpei.in. and arai-yasuyuki.in.	US-PGPUB	, 2003/06/12 11:17
US-PGPUR; EPG; JPG; DRRWENT; IDM TOB   US-PGPUB; EPG; JPG; DRRWENT; IDM TOB   USPAT; USP			, and organic		
US-PGPUR; EPG; JPG; DRRWENT; IDM TOB   US-PGPUB; EPG; JPG; DRRWENT; IDM TOB   USPAT; USP	'	' 9	"passivation film 847"	USPAT:	2003/06/12 10:56
Passivation film 847 is formed on the anode layer 846"   USPAT: US-FGFUB: EPO; JPO: DERMENT: IBM TOB USFAT: USFGFUB: EPO; JP		4			
DERWENT; IDM TOB   USPAT;   2003/06/12 11:01   USPAT;   USPOPUB;   EPO; JPO;   DERWENT;   LEPO; JPO;			1		
TDM TOB	1				I .
-   0   massivation film 847 is formed on the anode layer 846"   USPAT;   EPO; JPO;   DERMENT;   IBM TDB   USPAT;   US		1			
-   0   massivation film 847 is formed on the anode layer 846"   USPAT;   EPO; JPO;   DERMENT;   IBM TDB   USPAT;   US				IBM TDB	1
anode layer 846"			"massivation film 847 is formed on the		2003/06/12 11:01
					1 -5557 007 12 11.01
DERWENT: IBM 7DB			anude tayer 640"		
184 708		1	I	EPO; JPO;	1
184 708				DERWENT;	
-   0   "passivation film 847 is formed on the use   OSPAT: anode layer 846."					
anode layer 846."   US-PGPUB; EPG; JPG; DERMENT: 18M 7DB   USFAT: US-PGPUB; EPG; JPG; DERMENT: 18M 7DB   USFAT:	£	1 0	Hannaisstian film 847 to formed		2002/06/12 10:52
1420   semiconductor adj device adj method adj   USFAT;   2003/06/12   11:00   USFAT;   USFOCHUBE,   USFAT;   USFAT;   USFOCHUBE,   USFAT;   USFOCHUBE,   USFAT;	_	U			2003/06/12 10:5/
1420   semiconductor adj device adj method adj   USPAT;   2003/06/12 11:00   USPAT;   USPAC;   USPAC	1	1	, anode layer 846."		
1420   semiconductor adj device adj method adj   USPAT;   2003/06/12 11:00   USPAT;   USPAC;   USPAC	1			EPO: JPO:	2
1420   semiconductor adj device adj method adj   USPAT;   US-ECPUB;   EPO; JPO;   DERMENT;   IBM_TDB   USPAT;   US-ECPUB;   EPO; JPO;   DERMENT;   IBM_TDB   USPAT;   US-ECPUB;   EPO; JPO;   DERMENT;   IBM_TDB   USPAT;   US-ECPUB;   EPO; JPO;   DERMENT;   US-ECPUB;   US-ECPUB;   EPO; JPO;   DERMENT;   US-ECPUB;   US-EC					
1420   semiconductor adj device adj method adj   USFAT;   1003/06/12   11:00   USFAT;   1005-F05UB;   EPO; JPO;   DERMENT;   10M   TDB   USFAT;   USFACRUBA,   10M	1				t .
Tabricating		*	1		
Property	-	1 1420	semiconductor adj device adj method adj	USPAT;	1 2003/06/12 11:00
Property	1		fabricating	US-PGPUB:	
T45   Semiconductor ad   device adj method ad   USPAT;   1003/06/12   11:01   USPAT;   USPA		4		EPO: JPO:	1
TBM TDB	1		1		
- 745 semiconductor adj device adj method adj USPĀT; 108-PGFUB EPO; JPO; DERMENT; 108-PGFUB EPO; JPO; D		1	I .		1
fabricating.ti.	1				V.
Popular   Popu	-	745	, semiconductor ad device adj method adj	USPAT;	2003/06/12 11:01
Popular   Popu	1		fabricating ti	I IIS-PGPUB:	
DERMENT; INM TOB			1		1
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US-PCPUB; EPO; JPO; DERWENT; IBM TDB   US-PGPUB; EPO; JPO; DERWENT; IBM TDB   US-PGPUB   2003/06/12 11:16   user of the policy			I .	IBM TDB	
US-PCPUB; EPO; JPO; DERWENT; IBM TDB   US-PGPUB; EPO; JPO; DERWENT; IBM TDB   US-PGPUB   2003/06/12 11:16   user of the policy	-	1 0	"passivation film 847 is formed"	USPAT:	. 2003/06/12 11:02
Property	1	1			
DERMENT;   IBM TDB			t contract the contract to the		1
- 0					
-   0 yamazaki-shunpci.in. and arai-yasuyuki.in. US-FGFUB   and muakami-satoshi.in.   1 yamazaki-shunpci.in. and arai-yasuyuki.in.   203/06/12 11:16   and murakami-satoshi.in.   US-FGFUB   2003/06/12 11:16   and murakami-satoshi.in.   US-FGFUB   2003/06/12 11:16   and murakami-satoshi.in.   US-FGFUB   2003/06/12 15:56   (445/241). CCLS.   USFAT   2003/06/12 15:56   (445/241). CCLS.   USFAT   2003/06/12 16:07   (445/241). CLS.   USFAT   2003/06/12 16:07   (445/241). CLS.   USFAT	1			DERWENT;	
and munkami-satoshi.in.  1 yamazaki-shunpci.in. and srai-yasuyuki.in. and murakami-satoshi.in.  2171 ((313/512) or (313/504) or (313/500) or USFAT 2003/06/12 15:56 (313/512) or (313/504) or (313/500) or USFAT 2003/06/12 15:56 (315/64) or (313/504) or (313/500) or USFAT 2003/06/12 16:07 (315/64) or (315/64			·	IBM TDB	The state of the s
and munkami-satoshi.in.  1 yamazaki-shunpci.in. and srai-yasuyuki.in. and murakami-satoshi.in.  2171 ((313/512) or (313/504) or (313/500) or USFAT 2003/06/12 15:56 (313/512) or (313/504) or (313/500) or USFAT 2003/06/12 15:56 (315/64) or (313/504) or (313/500) or USFAT 2003/06/12 16:07 (315/64) or (315/64	1 _	1 0	l vamazaki-shuppoi in and arai-vasuunki in		. 2003/06/12 11:18
1 yamazaki-shunpci.in. and arai-yasuyuki.in.   US-PGFUB   2003/06/12 11:16   and murakami-satoshi.in.   US-PGFUB   2003/06/12 15:56   (445/24). CCLS.   USPAT   2003/06/12 15:56   (445/24). CCLS.   USPAT   2003/06/12 15:56   (445/24). CCLS.   USPAT   2003/06/12 16:07   (445/24). CCLS.   USPAT   USPAT   2003/06/12 16:07   (445/24). CCLS.   USPAT				0.0 1.01.00	, 2000/00/12 11:10
and murakami-satoshi.in.  - 2171 ((313/512) or (313/504) or (313/500) or (USPAT 2003/06/12 15:55 (145/24)).CCLS.  - 227 (OLED organic adj3 el adj3 (device display)).bi. and (fET field adj effect adj transistor).bi.  - 315 (OLED organic adj3 el adj3 (device display) organic adj2 (electroluminescent USPAT; US-PGPUB; EPO; PO FREWENT; display) organic adj2 (electroluminescent USPAT; 2003/06/12 16:05 (15:55 (1					1 0000 100 110 11 11
- (217) ((313/512) or (313/504) or (313/500) or (318/500) or (445/24)). CCLS (445/24)). CCLS (317) (OLED organic adj3 el adj3 (device display) bi. and (fET field adj effect adj transistor).bi. adj (device display) organic adj3 el adj3 (device display) organic adj2 (electroluminoscent USFAT: TBM TDB USFAT: EPO; JPO; DERWENT: TBM TDB USFAT: EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J	, -	1		US-PGPUB	ZUU3/06/12 11:18
- (217) ((313/512) or (313/504) or (313/500) or (318/500) or (445/24)). CCLS (445/24)). CCLS (317) (OLED organic adj3 el adj3 (device display) bi. and (fET field adj effect adj transistor).bi. adj (device display) organic adj3 el adj3 (device display) organic adj2 (electroluminoscent USFAT: TBM TDB USFAT: EPO; JPO; DERWENT: TBM TDB USFAT: EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J	40		and murakami-satoshi.in.	1	i
(445/24)).CCLS.  237. (OLED organic adj3 el adj3 (device display)).bi. and (fET field adj effect display)).bi. and (fET field adj effect display).bi. and (fET field adj effect display) organic adj2 electroluminacent display) organic adj2 (electroluminacent display) organic adj2 (electroluminacent display) organic adj3 el adj3 (device display) organic adj3 el adj3 (device display) organic adj2 (electroluminescent display) organic adj2 (electroluminescent display) organic adj2 (electroluminescent display) organic adj3 el adj3 (device display) organic adj2 (electroluminescent display) organic adj3 el adj3 (device display) organic adj2 (electroluminacent display) organic adj2 (electrolumi	-	2171	((313/512) or (313/504) or (313/500) or	. HSPAT	2003/06/12 15:58
- 237 (OLED organic adj3 el adj3 (device display)) bi. and (fET field adj effect adj transistor).bi 315 (OLED organic adj3 el adj3 (device display) organic adj2 (electroluminoscent UsrAT; TBM TDB Us		1 22/3	. (AAS (2A)) CCIS		1
display) bi. and (fET field adj effect   US-FGFUB;   EPO; JPO;   DRAWENT;   IBM TDB   USPAT;   2003/06/12 16:08   US-FGFUB;   EPO; JPO;   DRAWENT;   IBM TDB   USPAT;   2003/06/12 16:08   USPAT;   2003/06/12 16:08   USPAT;   EPO; JPO;   DRAWENT;   IBM TDB   USPAT;   EPO; JPO;   DEMENT;   IBM TDB   EPO; JPO;   DEMENT;   EPO; JPO;   DEMENT;   IBM TDB   EPO; JPO;   DEMENT;   EPO; JPO;   EPO; J				1	
adj transistor).bi.    Adj transistor).bi.   EPO; JPO; DERWENT; IBM TDB   USPAT;   USPAG;   USPAT;   EPO; JPO; DERWENT; IBM TDB   USPAT;   USPAG;	-	237			2003/06/12 16:07
adj transistor).bi.    Adj transistor).bi.   EPO; JPO; DERWENT; IBM TDB   USPAT;   USPAG;   USPAT;   EPO; JPO; DERWENT; IBM TDB   USPAT;   USPAG;			display)).bi. and (fET field adj effect	US-PGPUB;	T. Control of the Con
- 315 (OLED organic adj3 el adj3 (device US-PGFUB)   16M TDB   16M	1				
- 315 (OLED organic adj3 el adj3 (device USPÄT; 2003/06/12 16:08 electroluminescence)).bi. and (first field display) organic adj2 (electroluminescent USPAGT; 2003/06/12 16:08 electroluminescent olectroluminescent olectrolu			,,,		1
- 315 (OLED organic adj3 el adj3 (device display) organic adj2 (electroluminoscent USPÄT; 2003/06/12 16:08 electroluminoscent USPÄT; electroluminoscent DENONT; 2003/06/12 16:08 electroluminoscent DENONT; 2003/06/12 16:08 electroluminescent DENONT; 2003/06/12 16:08 electroluminescent EPO; JPO; JPO; DENONT; 2003/06/12 16:08 electroluminescent EPO; JPO; JPO; DENONT; 2003/06/12 16:08 electroluminescent EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J					
display) organic adj2 (electroluminoscent US-PGUB; electroluminoscence), bi. and (fbT field Gisplay) organic adj3 cl adj3 (device display) organic adj2 (electroluminescent USPAT; EPO; DEWENT; ISM TDB (display) organic adj2 (electroluminescent electroluminescent adj effect adj transistor), bi. and (fbT field Gisplay) organic adj3 el adj3 (device Gisplay) organic adj2 (electroluminescent Gisplay) organic ad					
display) organic adj2 (electroluminoscent US-PGUB; electroluminoscence), bi. and (fbT field Gisplay) organic adj3 cl adj3 (device display) organic adj2 (electroluminescent USPAT; EPO; DEWENT; ISM TDB (display) organic adj2 (electroluminescent electroluminescent adj effect adj transistor), bi. and (fbT field Gisplay) organic adj3 el adj3 (device Gisplay) organic adj2 (electroluminescent Gisplay) organic ad	' -	315	(OLED organic adj3 el adj3 (device	'USPAT;	2003/06/12 16:08
electroluminoscence).bi. and (fET field   EPO; JPO;   DERWENT;	1				
adj effect adj transistor).bi.    166 (OLED organic adj3 cl adj3 (device display) organic adj2 (electroluminescent electroluminescentel adj effect adj transistor),bi. and (fET field display) organic adj3 el adj3 (device display) organic adj3 el adj3 (device display) organic adj2 (electroluminescent electroluminescentel electroluminescence)),bi. and (fET field display) organic adj2 (electroluminescent electroluminescence)),bi. and (fET field display) organic adj2 (electroluminescent electroluminescentel), bi. and (fET field display) organic adj2 (electroluminescent electroluminescentel), bi. and (fET field display) organic adj2 (electroluminescent electroluminescentel), bi. and (fET field display) organic adj2 (electroluminescentel).	3				
- 166 (OLED organic adj3 cl adj3 (device USPAT: USPAT: 2003/06/12 16:08 display) organic adj2 (electroluminescent cleetroluminescent). bi. and (fET field adj effect adj transistor). bi. DEMUNT: 1BM TDB (COLED organic adj3 el adj3 (device USPAT: 1BM TDB USPAT: display) organic adj2 (electroluminescent EPO; JPO; delectroluminescent). bi. and (fET field DEMUNT: 1BM TDB USPAT: 2003/06/12 16:09 delectroluminescent EPO; JPO; DEWNNT: 1BM TDB USPAT: 2003/06/12 16:09 delectroluminescent EPO; JPO; DEWNNT: 1BM TDB USPAT: 2003/06/12 16:09 delectroluminescent EPO; JPO; DEWNNT: 1BM TDB USPAT: 2003/06/12 16:09 delectroluminescent DEWNT:					•
- 166 (OLED organic adj3 cl adj3 (device display) organic adj3 (electroluminescent clectroluminescent electroluminescence)).bi. and (fET field display) organic adj3 el adj3 (device display) organic adj3 el adj3 (device display) organic adj2 (electroluminescent EPO; JPO; 2003/06/12 16:05 electroluminescence)).bi. and (fET field display) organic adj2 (electroluminescent EPO; JPO; DERWRNT; adj effect adj transistor).bi.) and			auj ellect adj transistor).Dl.		1
display) organic adj2 (electroluminescent cleetroluminescent) bi. and (fET field DERWERT; adj effect adj transistor) bi.  98 ((OLED organic adj3 el adj3 (dovice USPAT; display) organic adj2 (electroluminescent EPO; JPO; display) organic adj2 (electroluminescent EPO; JPO; delectroluminescent) bi. and (fET field DERWERT; adj effect adj transistor) bi.) and [IBM_TDB]		1		IBM_TDB	2
display) organic adj2 (electroluminescent cleetroluminescent) bi. and (fET field DERWERT; adj effect adj transistor) bi.  98 ((OLED organic adj3 el adj3 (dovice USPAT; display) organic adj2 (electroluminescent EPO; JPO; display) organic adj2 (electroluminescent EPO; JPO; delectroluminescent) bi. and (fET field DERWERT; adj effect adj transistor) bi.) and [IBM_TDB]		166	(OLED organic adj3 cl adj3 (device	USPAT;	2003/06/12 16:08
clectroluminescence), bi. and (fET field DERWENT, adj effect adj transistor), bi.  - 98 '((OLFO orqanic adj3 el adj3 (device USFAT; 2003/06/12 16:05 display) organic adj2 (electroluminescent EFO; JPO: EFO; JPO: DERWENT, adj effect adj transistor), bi.) and [ET field DERWENT, adj effect adj transistor), bi.) and [EN TIBE TIBE TIBE TIBE TIBE TIBE TIBE TIBE					1
adj effect adj transistor).bi.  98 ((OLFD organic adj3 el adj3 (device USFAT; 2003/06/12 16:09 display) organic adj2 (electroluminescent EFO; JPO; electroluminescence)).bi. and (EET field DERWNNT; adj effect adj transistor).bi.) and IRM_TDB		'			
- 98'((OLFD orqanic adj3 el adj3 (device USFAT; 2003/06/12 16:05 display) organic adj2 (electroluminascent EPO; JPO; electroluminescence)).bi. and (fET field DERWRNT; adj effect adj transistor).bi.) and isM_TDB	1				•
display) organic adj2 (electroluminescent EPO; JPO; electroluminescence)).bi, and (fET field DERWENT; adj effect adj transistor).bi.) and IBM_TDB	7		adj effect adj transistor).bi.		i .
display) organic adj2 (electroluminescent EPO; JPO; electroluminescence)).bi, and (fET field DERWENT; adj effect adj transistor).bi.) and IBM_TDB	-	. 98	'((OLED organic adj3 el adj3 (device	. USPAT;	2003/06/12 16:09
'electroluminescence)).bi. and (fET field DERWENT: adj effect adj transistor).bi.) and IBM_TDB	1		display) organic adi2 (electroluminescent		
adj effect adj transistor).bi.) and IBM_TDB	1				i .
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(matrix matricos)				TRW_LDR	•
(mdctix mdctices)			(matrix matrices)		A. C.

	52 (((OLED organic adj3 el adj3 (device	USPAT;	2003/06/12 1	10:101
	display) organic adj2 (electroluminescent	'EPO; JPO;		1
1	electroluminescence)).bi. and (fET field	DERWENT;		1
4	'adj effect adj transistor).bi.) and	IBM_TDB	1	
1	(matrix matrices)) and (gas nitrogen	1		1
	krypton xenon argon neon helium)		'	1
	36 (((OLED organic adj3 el adj3 (device	USPAT;	2003/06/12 1	l6:27 .
i	display) organic adj2 (electroluminescent	: EPO; JPO;		
1	electroluminescence)).bi. and (fET field	DERWENT;		- 1
	adj effect adj transistor).bi.) and	IBM TDB	I .	Ī
	(matrix matrices)) and (gas nitrogen	-		
1	'krypton xenon argon neon helium) and (dry	7	1	1
	drving desiccant gctter)			î
	36 (US-6221553-S or US-6219113-S or	USPAT;	2003/06/12 1	16:18
1	US-6214520-\$ or US-6194119-\$ or	EPO; JPO;		
	'US-6157127-\$ or US-6140009-\$ or	DERWENT		Ĩ
	US-6114088-\$ or US-6103558-\$ or		1	
	.US-5935720-\$ or US-5908581-\$ or		L.	- 1
	US-5677546-\$ or US-5449582-\$ or	i		
	US-6284425-\$ or US-6270944-\$ or	1	T.	
	US-6242152-\$ or US-6228555-\$ or			1
1	US-6410201-\$ or US-6403809-\$ or	1	1	
	US-6372558-\$ or US-6358664-\$ or			1
	US-6351010-\$ or US-6346718-\$ or			
	US-6291126-\$ or US-6291116-\$ or	1	I .	
1	US-6521525-\$ or US-6518594-\$).did. or			1
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1	US-6468715-\$ or US-6429584-\$ or		1	
1	US-5405724-\$).did. or (EP-1089595-\$).did.	1		1
	or (JP-2001167877-\$).did. or	1	1	1
	L(EP-1089595-\$).did.		diameter and a second	'
i	10 (US-6221553-\$ or US-6219113-\$ or	USPAT;	2003/06/12	16:19
1	US-6214520-\$ or US-6194119-\$ or	EPO; JPO;		
	'US-6157127-\$ or US-6140009-\$ or	DERWENT	i .	,
	US-6114088-\$ or US-6103558-\$ or	1		
1	US-5935720-\$ or US-5908581-\$ or	1	'	
-1	US-5677546-\$ or US-5449582-\$ or		111	
	US-6284425-\$ or US-6270944-\$ or	1	1	1
	US-6242152-\$ or US-6228555-\$ or	1		7
1	US-6410201-\$ or US-6403809-\$ or	1	"	
	US-6372558-\$ or US-6358664-\$ or	1	1	
t t	US-6351010-\$ or US-6346718-\$ or		i	1
	US-6291126-\$ or US-6291116-\$ or	1		1
	US-6521525-\$ or US-6518594-\$).did. or	1	1	
1	US-6504215-\$ or US-6503831-\$ or		1	
1	US-6492190-\$ or US-6482564-\$ or		1	
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10 (((US-6221553-\$ or US-6219113-\$ or US-6214520-\$ or US-6194119-\$ or US-6157127-\$ or US-6140009-\$ or US-6114088-\$ or US-6103558-\$ or US-5935720-\$ or US-5908581-\$ or US-5677546-\$ or US-5449582-\$ or US-6284425-\$ or US-6270944-\$ or US-6242152-\$ or US-6228555-\$ or US-6410201-\$ or US-6403809-\$ or US-6372558-\$ or US-6358664-\$ or US-6351010-\$ or US-6346718-\$ or US-6291126-\$ or US-6291116-\$ or US-6521525-\$ or US-6518594-\$).did. or (US-6504215-\$ or US-6503831-\$ or US-6492190-\$ or US-6482564-\$ or US-6468715-\$ or US-6429584-\$ or US-5405724-\$).did. or (EP-1089595-\$).did. or (JP-2001167877-\$).did. or